/ Descriptions

SOT-23 NPN Silicon NPN transistor in a SOT-23 Plastic Package.

/ Features

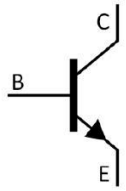
2SB709A

Complementary pair with 2SB709A.

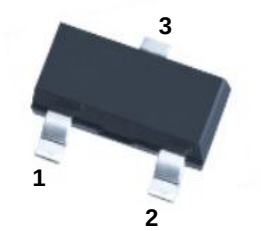
/ Applications

General power amplifier applications

/ Equivalent Circuit



/ Pinning



PIN1 Base PIN 2 Emitter PIN 3 Collector

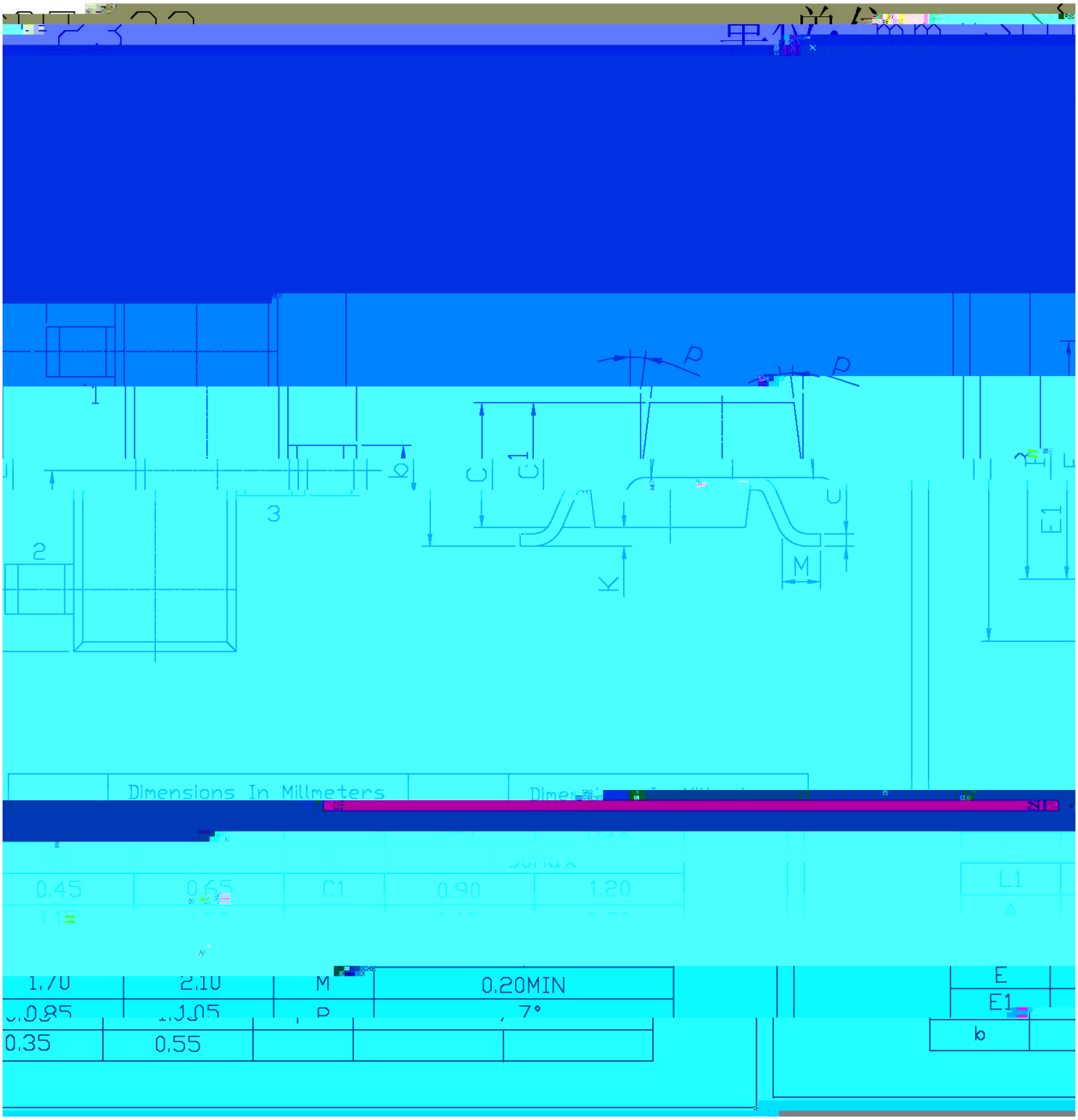
/ h_{FE} Classifications & Marking

h_{FE} Classifications Symbol	Q	R	S
h_{FE} Range	160-260	210-340	290-460
Marking	H1ZQ	H1ZR	H1ZS

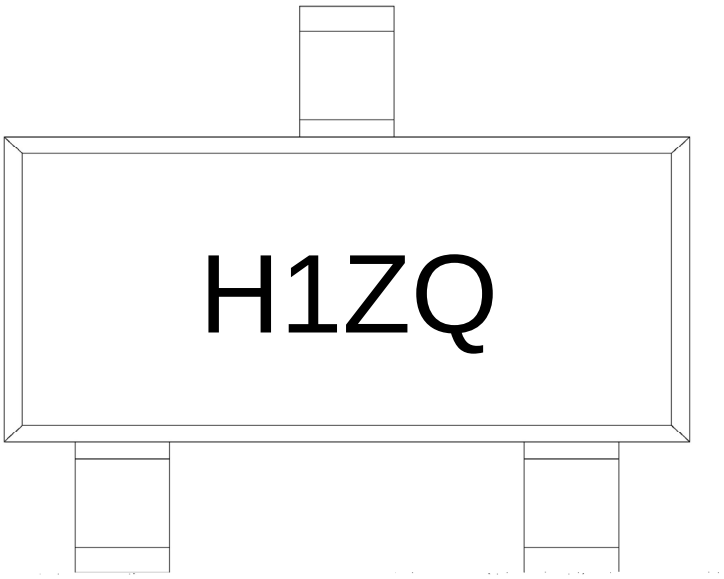
Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	60	V
Collector to Emitter Voltage	V_{CEO}	50	V
Emitter to Base Voltage	V_{EBO}	7.0	V
Collector Current	I_C	100	mA
Collector Current	I_{CP}	200	mA
Collector Power Dissipation	P_C	200	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector Cut-Off Current	I_{CBO}	V_{CB}=20V I_E=0			0.1	μA
Emitter Base Cut-Off Current	I_{EBO}	V_{CE}=10V I_B=0			100	μA
Collector-Base Breakdown Voltage	V_{CBO}	I_C=10				

/ Package Dimensions



/ Marking Instructions



H

1Z

Q: h_{FE}

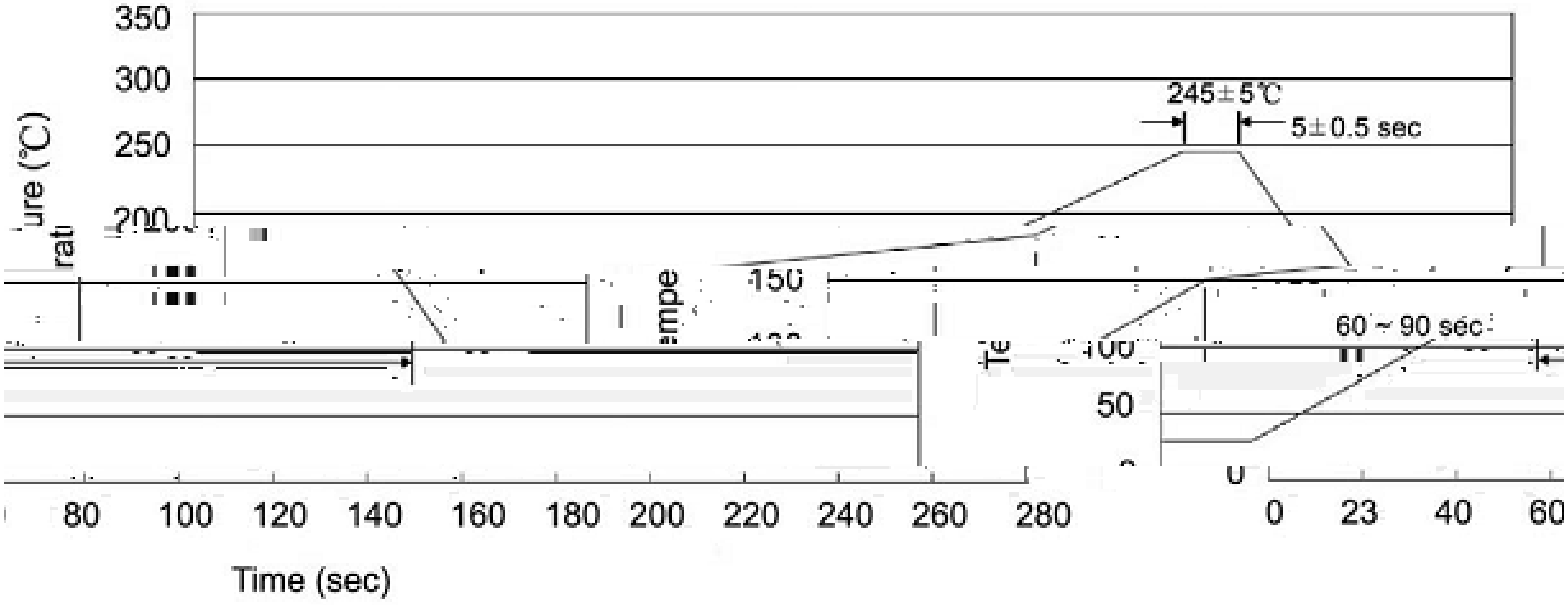
Note:

H: Company Code

1Z: Product Type Code

Q: h_{FE} Classifications Symbol Code

( ) / Temperature Profile for IR Reflow Soldering(Pb-Free)



Note:

1 25 150 60 90sec;	1.Preheating:25~150 , Time:60~90sec.
2 245±5 5±0.5sec;	2.Peak Temp.:245±5 , Duration:5±0.5sec.
3 2 10 /sec.	3. Cooling Speed: 2~10 /sec.

/ Resistance to Soldering Heat Test Conditions

260±5	10±1 sec.	Temp.:260±5	Time:10±1 sec

/ Packaging SPEC.

/ REEL

Package Type	Units	Dimension (unit mm^3)

„ „ 7